

2SD2134

加急出货

Silicon NPN Epitaxial Planar Type

AF Driver, High Power Amplifier
Complementary Pair with 2SB1414

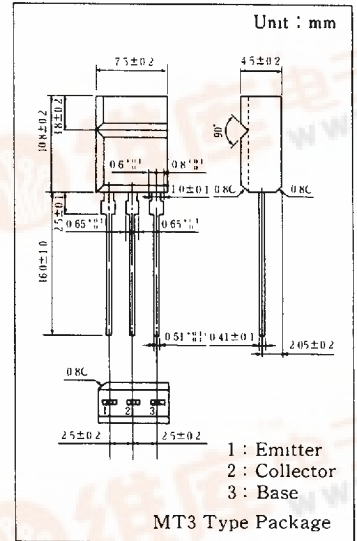
■ Features

- Very good linearity of DC current gain (h_{FE})
- High transition frequency (f_T)
- Optimum for the driver of 60~100W in complementary pair with 2SB1414

■ Absolute Maximum Ratings (Ta=25°C)

| Item | Symbol | Value | Unit |
|-----------------------------|-----------|------------|------|
| Collector-base voltage | V_{CBO} | 180 | V |
| Collector-emitter voltage | V_{CEO} | 180 | V |
| Emitter-base voltage | V_{EBO} | 5 | V |
| Peak collector current | I_{CP} | 1.5 | A |
| Collector current | I_C | 1 | A |
| Collector power dissipation | P_C | 1.5 | W |
| Junction temperature | T_J | 150 | °C |
| Storage temperature | T_{stg} | -55 ~ +150 | °C |

■ Package Dimensions



■ Electrical Characteristics (Tc=25°C)

| Item | Symbol | Condition | min. | typ. | max. | Unit |
|--------------------------------------|---------------|---|------|------|------|------|
| Collector-emitter voltage | V_{CBO} | $I_C = 100\mu A$ | 180 | | | V |
| Emitter-base voltage | V_{EBO} | $I_E = 10\mu A, I_C = 0$ | 5 | | | V |
| DC current gain | h_{FE1}^* | $V_{CE} = 10V, I_C = 150mA$ | 90 | 160 | 330 | |
| | h_{FE2} | $V_{CE} = 5V, I_C = 500mA$ | 50 | | | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 500mA, I_B = 50mA$ | | 0.5 | 2 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C = 500mA, I_B = 50mA$ | | 1 | 2 | V |
| Transition frequency | f_T | $V_{CB} = 10V, I_E = -50mA, f = 200MHz$ | | 200 | | MHz |
| Collector output capacitance | C_{ob} | $V_{CB} = 10V, I_E = 0, f = 1MHz$ | | 20 | | pF |

* h_{FE1} Classifications

| Class | Q | R | S |
|-----------|----------|-----------|-----------|
| h_{FE1} | 90 ~ 155 | 130 ~ 220 | 185 ~ 330 |



